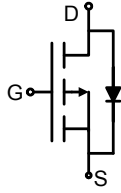
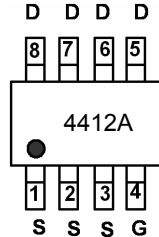
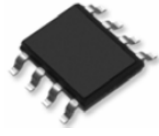


N-Channel Enhancement Mode Power MOSFET

<p>Description The HM4412A uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch and PWM applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● $V_{DS} = 30V, I_D = 7.0A$ $R_{DS(ON)} < 31m\Omega @ V_{GS}=10V$ $R_{DS(ON)} < 43m\Omega @ V_{GS}=4.5V$ ● High Power and current handling capability ● Lead free product is acquired ● Surface mount package <p>Application</p> <ul style="list-style-type: none"> ● Load switch ● PWM application 	<div style="text-align: center;">  <p>Schematic diagram</p>  <p>Marking and pin Assignment</p>  <p>SOP-8 top view</p> </div>
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Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
4412A	HM4412A	SOP8	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	7.0	A
Drain Current-Pulsed (Note 1)	I_{DM}	28	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$	-	25.5	31	m Ω
		$V_{GS}=4.5V, I_D=4A$	-	34	43	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	255	-	PF
Output Capacitance	C_{oss}		-	45	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.5	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14.5	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5A,$ $V_{GS}=10V$	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	0.85	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	5	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

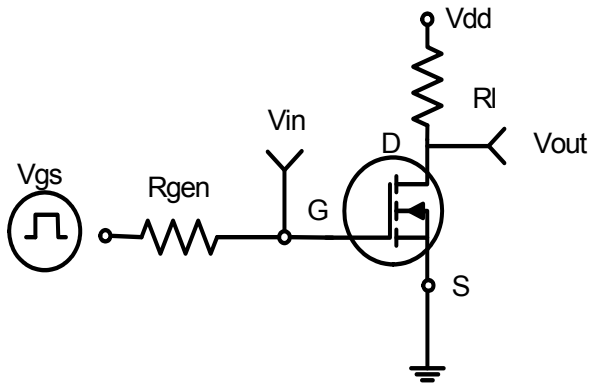


Figure 1: Switching Test Circuit

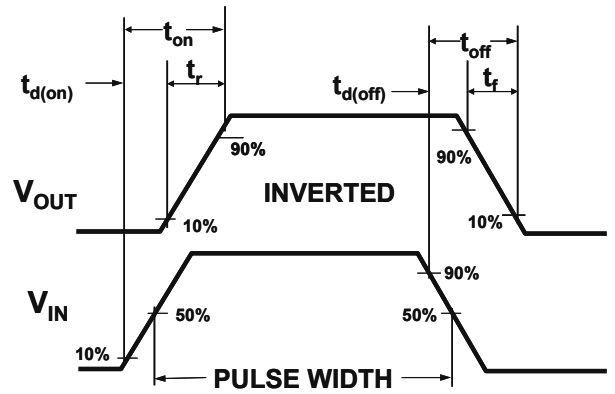


Figure 2: Switching Waveforms

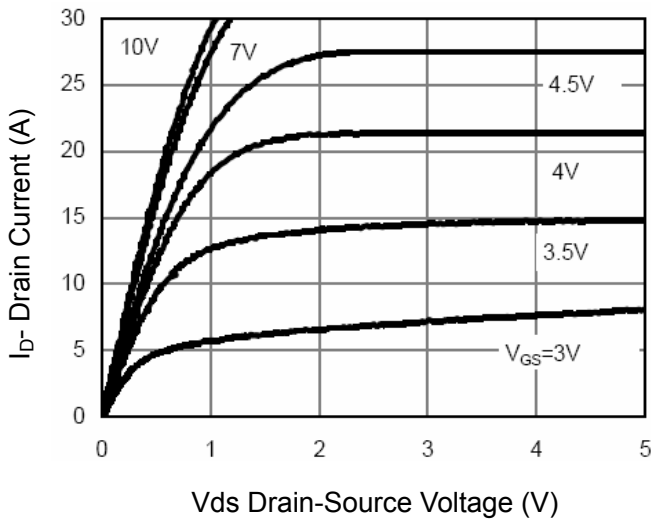


Figure 3 Output Characteristics

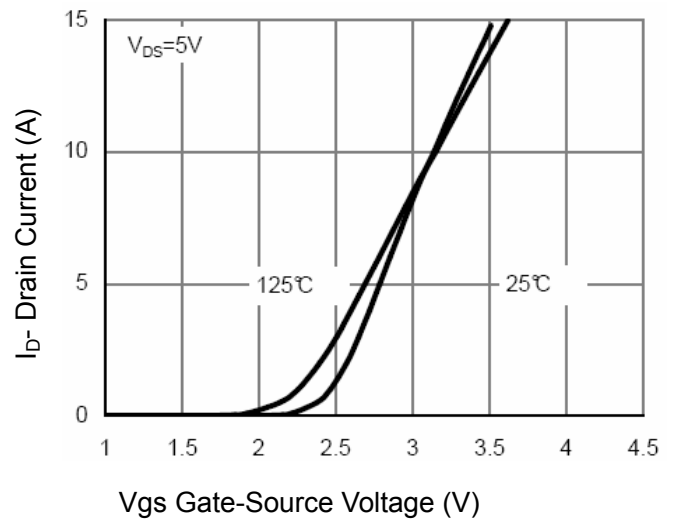


Figure 4 Transfer Characteristics

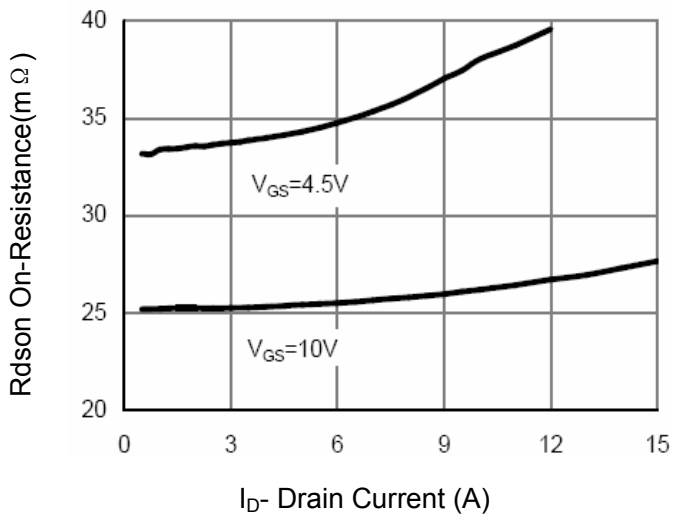


Figure 5 Drain-Source On-Resistance

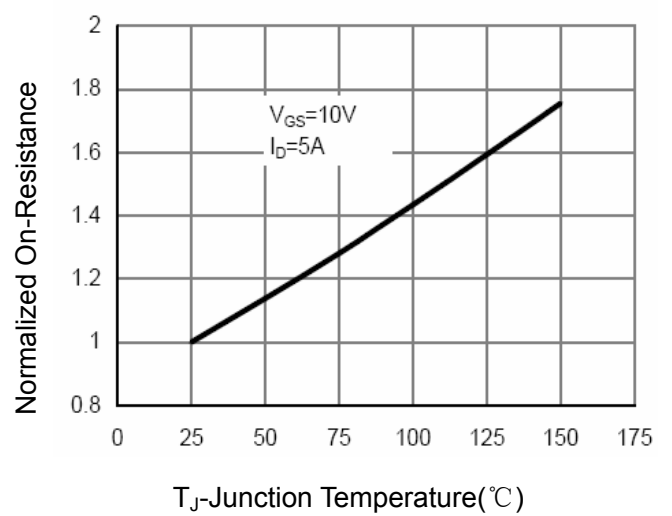
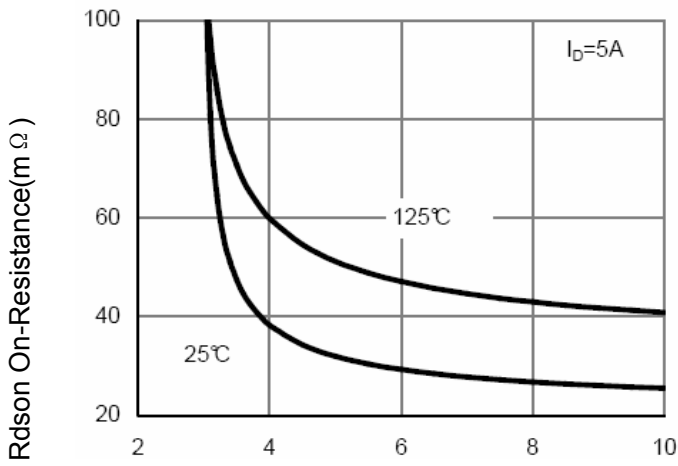
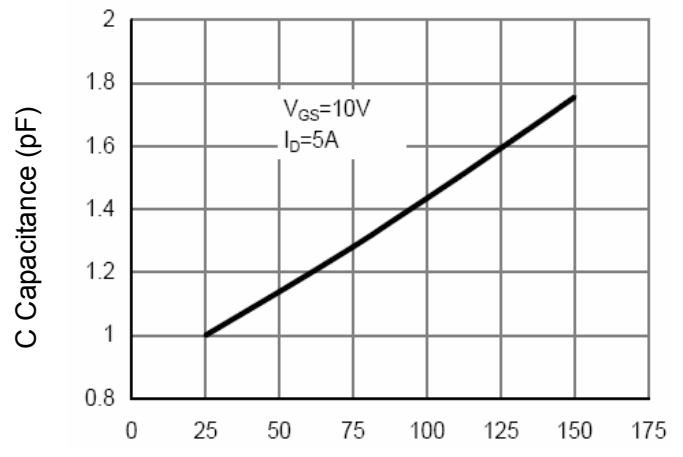


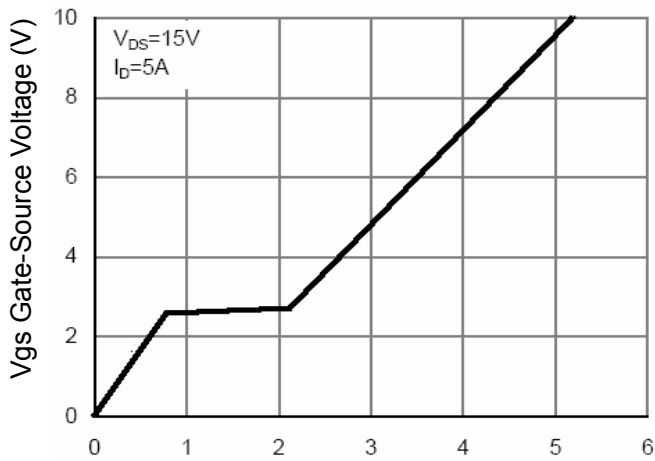
Figure 6 Drain-Source On-Resistance



Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



T_J-Junction Temperature(°C)
Figure 8 Drain-Source On-Resistance



Qg Gate Charge (nC)
Figure 9 Gate Charge

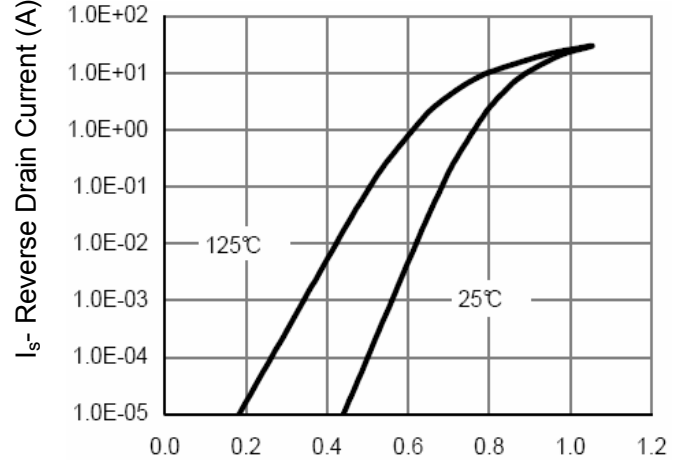
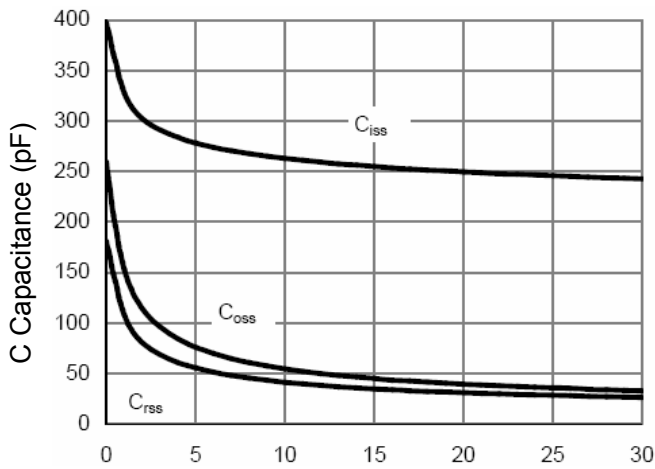


Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds

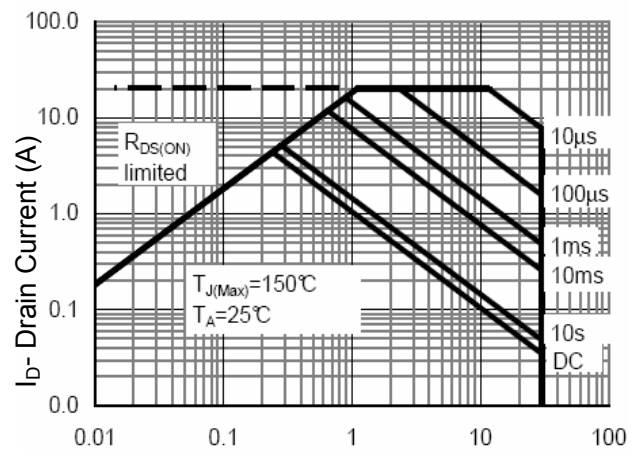


Figure 12 Safe Operation Area

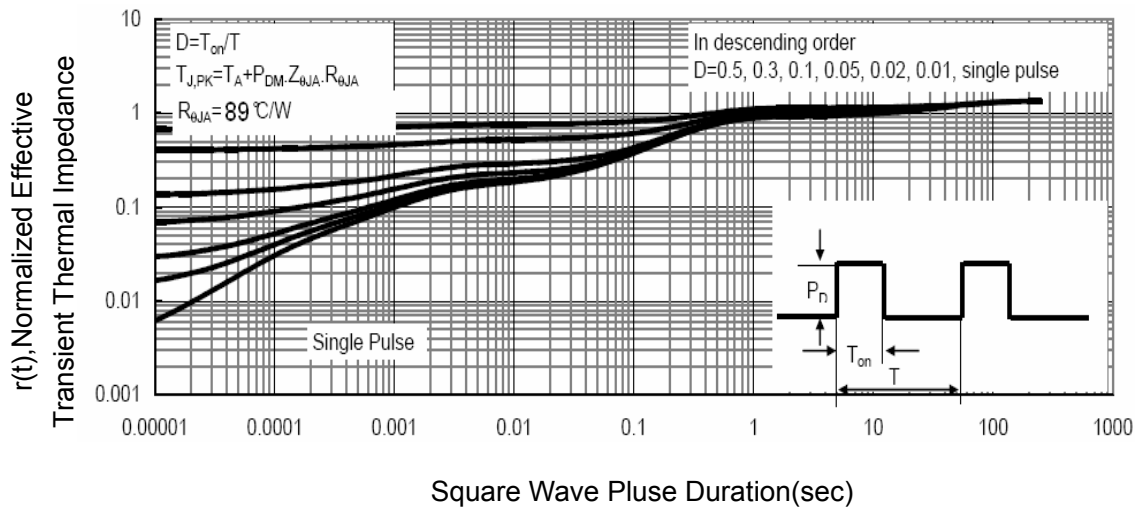
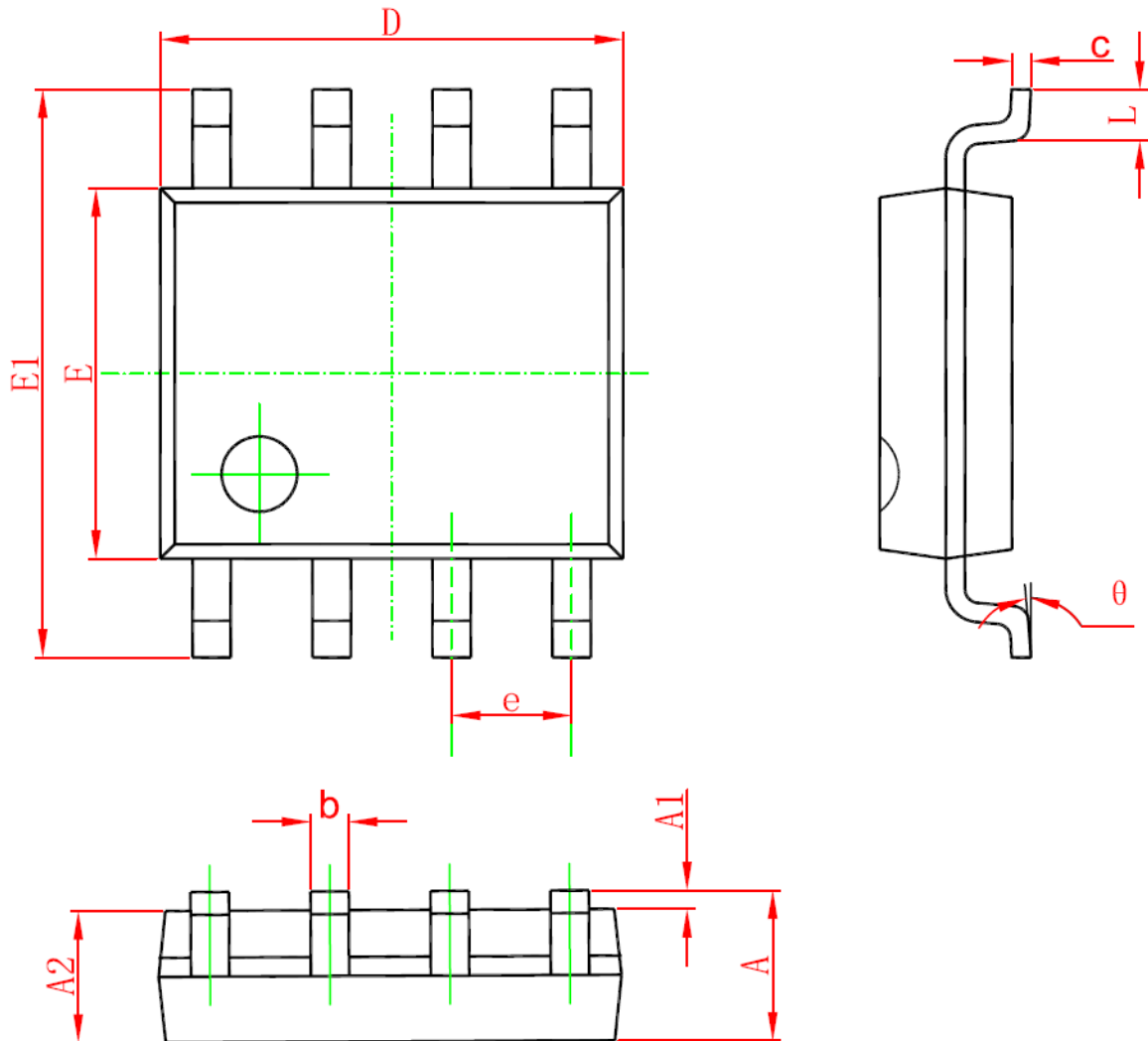


Figure 13 Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE IN FORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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